Seat No.:	Enrolment No

GUJARAT TECHNOLOGICAL UNIVERSITY BE –SEMESTER 1&2(NEW SYLLABUS)EXAMINATION- WINTER 2018

DE -SEMESTER 1&2(NEW STELADUS)EAAMINATION- WINTER 2016

Subj	ect (Code: 3110018 Date: 04-01-	2019
Subj	ect I	Name: Physics	
Tim	e: 10	:30 am to 01:00 pm Total Mark	s: 70
Instru	ıction	s:	
	2.	Attempt all questions. Make suitable assumptions wherever necessary. Figures to the right indicate full marks.	
Q.1	(a)	•	03
	(b)	· · · · · · · · · · · · · · · · · · ·	04
	(c)	What is photovoltaic effect. Explain construction and working of solar cell.	07
Q.2	(a)	Give difference between N type and P type semiconductors.	03
	(b)	•	04
	(c)	Explain Kronig Penney model in detail. OR	07
	(c)	Explain properties of superconductors.	07
Q.3	(a)	<u> </u>	03
	(b)	•	04
	(c)	Explain classification of materials as conductors, insulators and semiconductors.	07
		OR	
Q.3	(a)	Give difference between intrinsic and extrinsic semiconductors.	03
	(b)	•	04
0.4	(c)	Explain direct and indirect band gap with E-k diagrams.	07
Q.4	(a)	Define superconductivity and critical temperature.	03
	(b)	Discuss fermi golden rule. Explain diffusion machanism in detail	04
	(c)	Explain diffusion mechanism in detail. OR	07
Q.4	(a)		03
~··	(b)		04
		Explain experimental procedure for DLTS.	07
Q.5	(a)	The critical temperature of Nb is 9.15 K. At zero kelvin, the critical field is 0.196 T. Calculate the critical field at 6 K.	03
	(b)	Explain Drude model.	04
	(c)	Why two probe method for resistivity measurement failed and hence	07
	(6)	explain four probe method.	07
		OR	
Q.5	(a)	Give success and drawback of classical free electron theory.	03
	(b)	Derive expression of electron concentration in conduction band.	04
	(c)	Discuss UV – VIS method for band gap measurement of semiconductors.	07
